SPDT, 3 Ω R_{ON} Switch

The NLASB3157 is an advanced CMOS analog switch fabricated with silicon gate CMOS technology. It achieves very low propagation delay and RDSON resistances while maintaining CMOS low power dissipation. Analog and digital voltages that may vary across the full power-supply range (from V_{CC} to GND). This device is a drop in replacement for the NC7SB3157.

The select pin has overvoltage protection that allows voltages above V_{CC}, up to 7.0 V to be present on the pin without damage or disruption of operation of the part, regardless of the operating voltage.

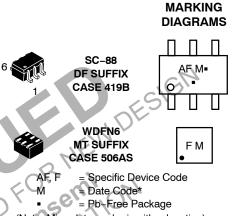
Features

- High Speed: $t_{PD} = 1.0 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2.0 \ \mu A$ (Max) at $T_A = 25^{\circ}C$
- Standard CMOS Logic Levels
- High Bandwidth, Improved Linearity
- Switches Standard NTSC/PAL Video, Audio, SPDIF and HDTV
- May be used for Clock Switching, Data Multiplexing, etc.
- R_{ON} Typical = 3 Ω @ V_{CC} = 4.5 V
- Break Before Make Circuitry, Prevents Inadvertent Shorts
- OT RECOMM SECONTAC • 2 Devices can Switch Balanced Signal Pairs, e.g. LVDS > 200 Mb/s
- Latchup Performance Exceeds 300 mA
- Pin for Pin Drop in for NC7SB3157
- Tiny SC88 and WDFN6 Packages
- ESD Performance:
 - Human Body Model; > 2000 V;
 - ♦ Machine Model; > 200 V
- NLVASB3157 Features Extended Automotive Temperature Range; -55°C to +125°C (See Appendix A)
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



ON Semiconductor®

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(Note: Microdot may be in either location) Date Code orientation may vary depending upon manufacturing location.

FUNCTION TABLE

Select Input	Function
L	B0 Connected to A
Н	B1 Connected to A

ORDERING INFORMATION

Device	Package	Shipping [†]
NLASB3157DFT2G	SC-88 (Pb-Free)	3000 / Tape & Reel
NLVASB3157DFT2G	SC–88 (Pb–Free)	3000 / Tape & Reel
NLASB3157MTR2G	WDFN6 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ATIVEFC

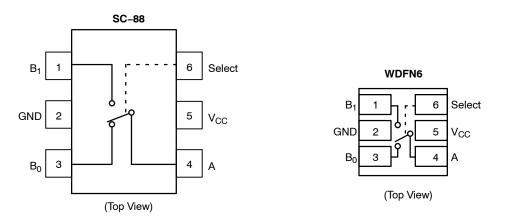


Figure 1. Pin Assignment & Logic Diagram

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MAXIMUM RATINGS

Rating	Symbol	Value	ິ Unit
Supply Voltage	V _{CC}	-0.5 to +7.0	V
DC Switch Voltage (Note 1)	V _{IS}	-0.5 to V _{CC} + 0.5	V
DC Input Voltage (Note 1)	V _{IN}	-0.5 to + 7.0	V
DC Input Diode Current @ V _{IN} < 0 V	ЧК	-50	mA
DC Input / Output Current	Ιουτ	128	mA
DC V _{CC} or Ground Current	Icc/I _{GND}	+100	mA
Storage Temperature Range	Tstg	-65 to +150	°C
Junction Temperature Under Bias	O TKO	150	°C
Junction Lead Temperature (Soldering, 10 Seconds)	47	260	°C
Power Dissipation @ +85°C	PD	180	mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. The input and output negative voltage ratings may be exceeded if the input and output diode current ratings are observed.

RECOMMENDED OPERATING CONDITIONS (Note 2)

Characteristic S	Symbol	Min	Max	Unit
Supply Voltage Operating	V _{CC}	1.65	5.5	V
Select Input Voltage	V _{IN}	0	5.5	V
Switch Input Voltage	V _{IS}	0	V _{CC}	V
Output Voltage	V _{OUT}	0	V _{CC}	V
Operating Temperature	T _A	-55	+125	°C
Input Rise and Fall Time Control Input V_{CC} = 2.3 V–3.6 V Control Input V_{CC} = 4.5 V–5.5 V	t _r , t _f	0 0	10 5.0	ns/V
Thermal Resistance	θ_{JA}	-	350	°C/W

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.
 Select input must be held HIGH or LOW, it must not float.

DC ELECTRICAL CHARACTERISTICS - NLASB3157

			V _{cc}	1	T _A = +25°C	;	T _A = -40°C	C to +85°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Unit
V _{IH}	HIGH Level Input Voltage		1.65–1.95 2.3–5.5				0.75 V _{CC} 0.7 V _{CC}		V
V _{IL}	LOW Level Input Voltage		1.65–1.95 2.3–5.5					0.25 V _{CC} 0.3 V _{CC}	V
I _{IN}	Input Leakage Current	$0 \le V_{IN} \le 5.5 \text{ V}$	0–5.5		±0.05	±0.1		±1	μA
I _{OFF}	OFF State Leakage Current	$0 \le A, B \le V_{CC}$	1.65–5.5		±0.05	±0.1		±1	μA
R _{ON}	Switch On Resistance (Note 3)		4.5		3.0 5.0 7.0			7.0 12 15	Ω
		$V_{IN} = 0 V$, $I_O = 24 mA$ $V_{IN} = 3 V$, $I_O = -24 mA$	3.0		4.0 10			9.0 20	Ω
		$V_{IN} = 0 V$, $I_O = 8 mA$ $V_{IN} = 2.3 V$, $I_O = -8 mA$	2.3		5.0 13			12 30	Ω
		$V_{IN} = 0 V$, $I_O = 4 mA$ $V_{IN} = 1.65 V$, $I_O = -4 mA$	1.65		6.5 17		NOT	20 50	Ω
I _{CC}	Quiescent Supply Current All Channels ON or OFF	V _{IN} = V _{CC} or GND I _{OUT} = 0	5.5		FC	Roll	10,1	10	μA
	Analog Signal Range		V _{CC}	0		Vcc	0	V _{CC}	V
R _{RANGE}	On Resistance Over Signal Range (Note 3) (Note 7)	$\begin{split} I_{A} &= -30 \text{ mA}, \ 0 \leq V_{Bn} \\ &\leq V_{CC} \\ I_{A} &= -24 \text{ mA}, \ 0 \leq V_{Bn} \end{split}$	4.5 3.0	ENO	JRC	RM		25 50	Ω
		\leq V _{CC} I _A = -8 mA, 0 \leq V _{Bn} \leq V _{CC}	2.3	COR				100	
	C	$I_A = -4 \text{ mA}, 0 \leq V_{Bn}$ $\leq V_{CC}$	1.65					300	
∆R _{ON}	On Resistance Match Between Channels (Note 3) (Note 4) (Note 5)	$\begin{array}{l} I_A = -30 \text{ mA}, \ V_{Bn} = 3.15 \\ I_A = -24 \text{ mA}, \ V_{Bn} = 2.1 \\ I_A = -8 \text{ mA}, \ V_{Bn} = 1.6 \\ I_A = -4 \text{ mA}, \ V_{Bn} = 1.15 \end{array}$	4.5 3.0 2.3 1.65		0.15 0.2 0.5 0.5				Ω
R _{flat}	On Resistance Flatness (Note 3) (Note 4) (Note 6)	$I_A = -30 \text{ mA}, 0 \le V_{Bn}$ $\le V_{CC}$ $I_A = -24 \text{ mA}, 0 \le V_{Bn}$	5.0 3.3		6.0 12				Ω
<		\leq V _{CC} I _A = -8 mA, 0 \leq V _{Bn}	2.5		28				
		\leq V _{CC} I _A = -4 mA, 0 \leq V _{Bn} \leq V _{CC}	1.8		125				

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Measured by the voltage drop between A and B pins at the indicated current through the switch. On Resistance is determined by the lower

of the voltages on the two (A or B Ports). 4. Parameter is characterized but not tested in production.

ΔR_{ON} = R_{ON} max – R_{ON} min measured at identical V_{CC}, temperature and voltage levels.
 Flatness is defined as the difference between the maximum and minimum value of On Resistance over the specified range of conditions.

7. Guaranteed by Design.

			V _{cc}	Τ ₄	ς = +25°	C	T _A = -40°C	C to +85°C		Figure
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Unit	Number
t _{PHL} t _{PLH}	Propagation Delay Bus to Bus (Note 9)	V _I = OPEN	1.65–1.95 2.3–2.7 3.0–3.6 4.5–5.5					1.2 0.8 0.3	ns	Figures 2, 3
t _{PZL} t _{PZH}	Output Enable Time Turn On Time (A to B _n)	$\label{eq:VI} \begin{array}{l} V_I = 2 \times V_{CC} \text{ for } t_{PZL} \\ V_I = 0 V \text{ for } t_{PZH} \end{array}$	1.65–1.95 2.3–2.7 3.0–3.6 4.5–5.5			23 13 6.9 5.2	7.0 3.5 2.5 1.7	24 14 7.6 5.7	ns	Figures 2, 3
t _{PLZ} t _{PHZ}	Output Disable Time Turn Off Time (A Port to B Port)	$\label{eq:VI} \begin{array}{l} V_I = 2 \times V_{CC} \text{ for } t_{PLZ} \\ V_I = 0 V \text{ for } t_{PHZ} \end{array}$	1.65–1.95 2.3–2.7 3.0–3.6 4.5–5.5			12.5 7.0 5.0 3.5	3.0 2.0 1.5 0.8	13 7.5 5.3 3.8	ns	Figures 2, 3
t _{B-M}	Break Before Make Time (Note 8)		1.65–1.95 2.3–2.7 3.0–3.6 4.5–5.5				0.5 0.5 0.5 0.5		ns	Figure 4
Q	Charge Injection (Note 8)	$\begin{array}{l} C_{L} = 0.1 \; nF, V_{GEN} = 0 \; V \\ R_{GEN} = 0 \; \Omega \end{array}$	5.0 3.3		7.0 3.0			NOF	рС	Figure 5
OIRR	Off Isolation (Note 10)	R _L = 50 Ω f = 10 MHz	1.65–5.5		-57		2 11		dB	Figure 6
Xtalk	Crosstalk	R _L = 50 Ω f = 10 MHz	1.65–5.5		-54	50	sent	101	dB	Figure 7
BW	-3 dB Bandwidth	$R_L = 50 \Omega$	1.65-5.5	16.	250	⁷ 0,	MA		MHz	Figure 10
THD	Total Harmonic Distortion (Note 8)	$R_{L} = 600 \Omega$ 0.5 V _{P-P} f = 600 Hz to 20 kHz	5.0	57	9.011	SFC	K.		%	

AC ELECTRICAL CHARACTERISTICS - NLASB3157

CAPACITA	NCE - NLASB3157 (Note 11)	NTACFOR		I	I	
Symbol	Parameter	Test Conditions	Тур	Max	Unit	Figure Number
C _{IN}	Select Pin Input Capacitance	V _{CC} = 0 V	2.3		pF	
C _{IO-B}	B Port Off Capacitance	V _{CC} = 5.0 V	6.5		pF	Figure 8
C _{IOA-ON}	A Port Capacitance when Switch is Enabled	V _{CC} = 5.0 V	18.5		pF	Figure 9

8. Guaranteed by Design.
 9. This parameter is guaranteed by design but not tested. The bus switch contributes no propagation delay other than the RC delay of the On Resistance of the switch and the 50 pF load capacitance, when driven by an ideal voltage source (zero output impedance).

10. Off Isolation = 20 log₁₀ [V_A/V_{Bn}]. 11. T_A = +25°C, f = 1 MHz, Capacitance is characterized but not tested in production.

APPENDIX A

DC ELECTRICAL EXTENDED AUTOMOTIVE TEMPERATURE RANGE CHARACTERISTICS - NLVASB3157

			V _{cc}	Т	A = +25°0	C	T _A = -55°C	to +125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Unit
V _{IH}	HIGH Level Input Voltage		1.65–1.95 2.3–5.5				0.75 V _{CC} 0.7 V _{CC}		V
V _{IL}	LOW Level Input Voltage		1.65–1.95 2.3–5.5					0.25 V _{CC} 0.3 V _{CC}	V
I _{IN}	Input Leakage Current	$0 \le V_{IN} \le 5.5 V$	0–5.5		±0.05	±0.1		±1	μA
I _{OFF}	OFF State Leakage Current	$0 \le A, B \le V_{CC}$	1.65–5.5		±0.05	±0.1		±1	μA
R _{ON}	Switch On Resistance (Note 12)		4.5		3.0 5.0 7.0			8.5 13.0 15.0	Ω
		$V_{IN} = 0 \text{ V}, I_O = 24 \text{ mA}$ $V_{IN} = 3 \text{ V}, I_O = -24 \text{ mA}$	3.0		4.0 10			11 20	
		$V_{IN} = 0 \text{ V}, I_O = 8 \text{ mA}$ $V_{IN} = 2.3 \text{ V}, I_O = -8 \text{ mA}$	2.3		5.0 13		NDE	12 30	
		$V_{IN} = 0 \text{ V}, I_O = 4 \text{ mA}$ $V_{IN} = 1.65 \text{ V}, I_O = -4 \text{ mA}$	1.65		6.5 17	NE		20 50	
I _{CC}	Quiescent Supply Current All Channels ON or OFF	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0$	5.5	ED	FOR	1.0 6	1014	10	μΑ
	Analog Signal Range		Vcc	0	2 ~	Vcc	0	V _{CC}	V
R _{RANGE}	On Resistance Over Signal Range (Note 12) (Note 14)	$I_A = -30 \text{ mA}, 0 \le V_{Bn} \le V_{CC}$ $I_A = -24 \text{ mA}, 0 \le V_{Bn} \le V_{CC}$ $I_A = -8 \text{ mA}, 0 \le V_{Bn}$	4.5 3.0	00	<i>I</i> FO,			25 50	Ω
		$\leq V_{CC}$ $I_A = -4 \text{ mA}, 0 \leq V_{Bn}$ $\leq V_{CC}$	2.3)K				100	
			1.65					300	

12. Measured by the voltage drop between A and B pins at the indicated current through the switch. On Resistance is determined by the lower of the voltages on the two (A or B Ports).
13. Flatness is defined as the difference between the maximum and minimum value of On Resistance over the specified range of conditions.
14. Guaranteed by Design.

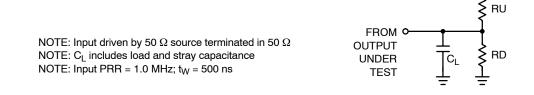
* For ΔR_{ON} , R_{FLAT} , Q, OIRR, Xtalk, BW, THD, and CIN see -40°C to 85°C section. 119

APPENDIX A AC ELECTRICAL EXTENDED AUTOMOTIVE TEMPERATURE RANGE CHARACTERISTICS – NLVASB3157

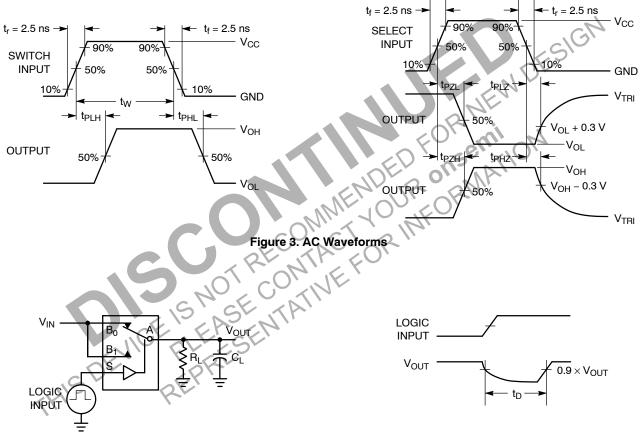
			V _{CC}	Τ ₄	(= +25	°C	T _A = -55°C	to +125°C		Figure
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Unit	Number
t _{PHL} t _{PLH}	Propagation Delay Bus to Bus (Note 16)	V _I = OPEN	1.65–1.95 2.3–2.7 3.0–3.6 4.5–5.5					1.2 0.8 0.3	ns	Figures 2, 3
t _{PZL} t _{PZH}	Output Enable Time Turn On Time (A to B _n)	$\label{eq:VI} \begin{array}{l} V_I = 2 \ \times \ V_{CC} \ \text{for} \ t_{PZL} \\ V_I = 0 \ V \ \text{for} \ t_{PZH} \end{array}$	1.65–1.95 2.3–2.7 3.0–3.6 4.5–5.5			23 13 6.9 5.2	7.0 3.5 2.5 1.7	24 14 9.0 7.0	ns	Figures 2, 3
t _{PLZ} t _{PHZ}	Output Disable Time Turn Off Time (A Port to B Port)	$\label{eq:VI} \begin{array}{l} V_{I} = 2 \ \times \ V_{CC} \ \text{for} \ t_{PLZ} \\ V_{I} = 0 \ V \ \text{for} \ t_{PHZ} \end{array}$	1.65–1.95 2.3–2.7 3.0–3.6 4.5–5.5			12.5 7.0 5.0 3.5	3.0 2.0 1.5 0.8	13 7.5 6.5 5.0	ns	Figures 2, 3
t _{B-M}	Break Before Make Time (Note 15)		1.65–1.95 2.3–2.7 3.0–3.6 4.5–5.5				0.5 0.5 0.5 0.5	DE	15	Figure 4
		y design but not tested. The 50 pF load capacitance, Ktalk, BW, THD, and Cl	COMMA ONTAC ONTAC	FC	OU R ^{II}	NFC				
A	THISDEVIC	REPRESE								

AC LOADING AND WAVEFORMS

γv_l









AC LOADING AND WAVEFORMS

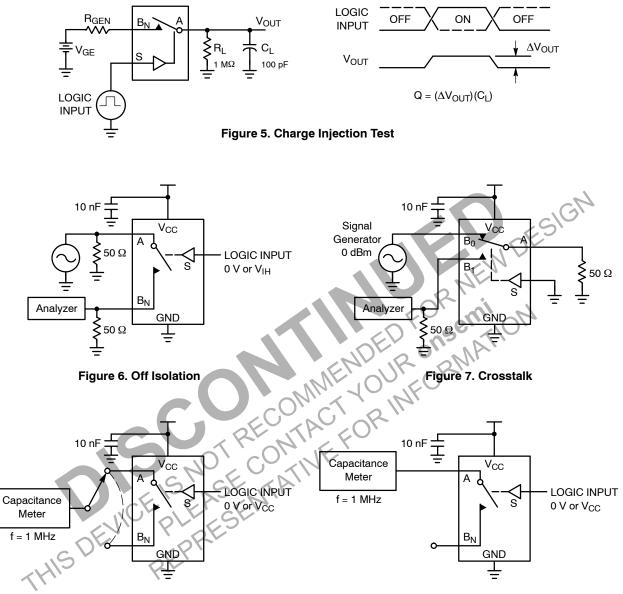


Figure 8. Channel Off Capacitance

Figure 9. Channel On Capacitance

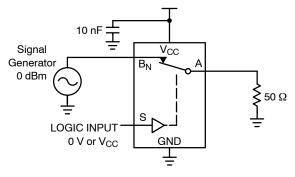
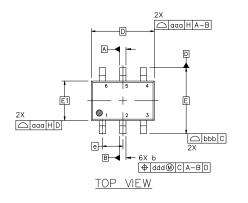


Figure 10. Bandwidth

semi

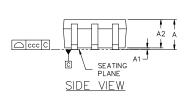
SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 **ISSUE Z**

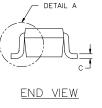
DATE 18 APR 2024

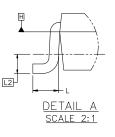


NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME 1. Y14.5-2018.
- 2.
- ALL DIMENSION ARE IN MILLIMETERS. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 3. PER END.
- 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF DATUMS A AND B ARE DETERMINED AT DATUM H.
- 5.
- DIMENSIONS & AND C APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. 6.
- DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION. 7 ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION & AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.







	MI	LLIMETER	S			
DIM	MIN.	NOM.	MAX.			
А			1.10			
A1	0.00		0.10			
A2	0.70	0.90	1.00			
b	0.15	0.20	0.25			
с	0.08	0.15	0.22			
D		2.00 BSC	;			
E		2.10 BSC				
E1		1.25 BSC	;			
е		0.65 BSC)			
L	0.26	0.36	0.46			
L2		0.15 BSC				
aaa		0.15				
bbb	0.30					
ccc		0.10				
ddd		0.10				

6X 0.66 6X 0.30-2.50 0.65 PITCH

RECOMMENDED MOUNTING FOOTPRINT*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

XXXM. . 0

GENERIC **MARKING DIAGRAM***

6

Μ

XXX = Specific Device Code

= Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42985B	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.						
DESCRIPTION:	SC-88 2.00x1.25x0.90, 0.65	5P	PAGE 1 OF 2					
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SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 ISSUE Z

DATE 18 APR 2024

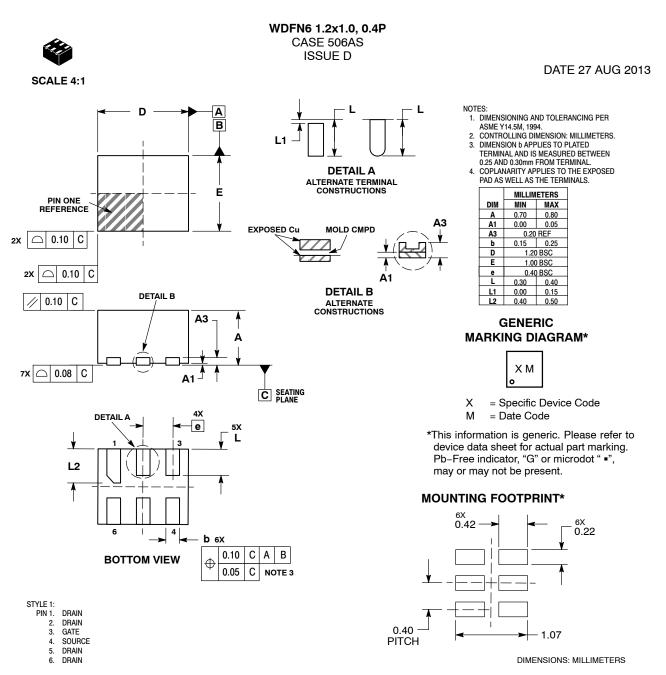
STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13:	STYLE 14:	STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:
PIN 1. ANODE	PIN 1. VREF	PIN 1. ANODE 1	PIN 1. BASE 1	PIN 1. BASE 1	PIN 1. VIN1
2. N/C	2. GND	2. ANODE 2	2. EMITTER 2	2. EMITTER 1	2. VCC
3. COLLECTOR	3. GND	3. ANODE 3	3. COLLECTOR 2	3. COLLECTOR 2	3. VOUT2
4. EMITTER	4. IOUT	4. CATHODE 3	4. BASE 2	4. BASE 2	4. VIN2
5. BASE	5. VEN	5. CATHODE 2	5. EMITTER 1	5. EMITTER 2	5. GND
6. CATHODE	6. VCC	6. CATHODE 1	6. COLLECTOR 1	6. COLLECTOR 1	6. VOUT1
STYLE 19:	STYLE 20:	STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:
PIN 1. I OUT	PIN 1. COLLECTOR	PIN 1. ANODE 1	PIN 1. D1 (i)	PIN 1. Vn	PIN 1. CATHODE
2. GND	2. COLLECTOR	2. N/C	2. GND	2. CH1	2. ANODE
3. GND	3. BASE	3. ANODE 2	3. D2 (i)	3. Vp	3. CATHODE
4. V CC	4. EMITTER	4. CATHODE 2	4. D2 (c)	4. N/C	4. CATHODE
5. V EN	5. COLLECTOR	5. N/C	5. VBUS	5. CH2	5. CATHODE
6. V REF	6. COLLECTOR	6. CATHODE 1	6. D1 (c)	6. N/C	6. CATHODE
STYLE 25:	STYLE 26:	STYLE 27:	STYLE 28:	STYLE 29:	STYLE 30:
PIN 1. BASE 1	PIN 1. SOURCE 1	PIN 1. BASE 2	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. SOURCE 1
2. CATHODE	2. GATE 1	2. BASE 1	2. DRAIN	2. ANODE	2. DRAIN 2
3. COLLECTOR 2	3. DRAIN 2	3. COLLECTOR 1	3. GATE	3. COLLECTOR	3. DRAIN 2
4. BASE 2	4. SOURCE 2	4. EMITTER 1	4. SOURCE	4. EMITTER	4. SOURCE 2
5. EMITTER	5. GATE 2	5. EMITTER 2	5. DRAIN	5. BASE/ANODE	5. GATE 1
6. COLLECTOR 1	6. DRAIN 1	6. COLLECTOR 2	6. DRAIN	6. CATHODE	6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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